

Thyristor Module

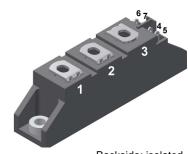
MCMA50P1200TA

V_{RRM}	<i>=</i> 2x 1200 V				
I _{tav}	=	50 A			
Vτ	=	1.17 V			

Phase leg

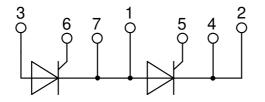
Part number

MCMA50P1200TA



Backside: isolated





Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al2O3-ceramic

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: TO-240AA

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

Disclaimer Notice

Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at www.littelfuse.com/disclaimer-electronics.

IXYS reserves the right to change limits, conditions and dimensions.



MCMA50P1200TA

Thyristo				1	Ratings		!
Symbol	Definition	Conditions		min.	typ.	max.	Uni
V _{RSM/DSM}	max. non-repetitive reverse/forwa	rd blocking voltage	$T_{vJ} = 25^{\circ}C$			1300	· ·
V _{RRM/DRM}	max. repetitive reverse/forward bl		$T_{vJ} = 25^{\circ}C$			1200	١
R/D	reverse current, drain current	V _{R/D} = 1200 V	$T_{vJ} = 25^{\circ}C$			100	μ
		V _{R/D} = 1200 V	$T_{vJ} = 140^{\circ}C$			6	m/
VT	forward voltage drop	$I_{T} = 50 \text{ A}$	$T_{VJ} = 25^{\circ}C$			1.25	١
		$I_{T} = 100 \text{ A}$				1.48	١
		$I_{T} = 50 \text{ A}$	T _{vJ} = 125°C			1.17	١
		$I_{T} = 100 \text{ A}$				1.44	١
I _{tav}	average forward current	T _c = 85°C	T _{vJ} = 140°C			50	1
T(RMS)	RMS forward current	180° sine				79	/
ν _{το}	threshold voltage		T _{v.i} = 140°C			0.89	١
r _τ	slope resistance } for power lo	oss calculation only	vo			5.3	m
R _{thJC}	thermal resistance junction to cas	e .				0.7	
R _{thCH}	thermal resistance case to heatsi				0.2	•••	K/V
P _{tot}	total power dissipation		$T_c = 25^{\circ}C$		0.2	160	٧
_	max. forward surge current	t = 10 ms; (50 Hz), sine	$T_{v_i} = 45^{\circ}C$			800	
TSM	max. Iorward burge burrent	t = 8,3 ms; (60 Hz), sine	$V_{\rm R} = 0 V$			865	
		t = 0.5 ms; (50 Hz), sine t = 10 ms; (50 Hz), sine	$\frac{v_{R}}{T_{V,I}} = 140^{\circ}C$			680	,
	under for funcion	t = 8,3 ms; (60 Hz), sine	$\frac{V_{R} = 0 V}{T_{R} + 1500}$			735	
l²t	value for fusing	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			3.20	
		t = 8,3 ms; (60 Hz), sine	$V_{R} = 0 V$			3.12	
		t = 10 ms; (50 Hz), sine	$T_{vJ} = 140 ^{\circ}\text{C}$			2.31	kA ²
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			2.25	kA ²
C	junction capacitance	$V_{R} = 400 V$ f = 1 MHz	$T_{vJ} = 25^{\circ}C$		32		pl
P _{GM}	max. gate power dissipation	t _P = 30 μs	$T_c = 140^{\circ}C$			10	۷
		t _P = 300 μs				5	۷
P _{GAV}	average gate power dissipation					0.5	۷
(di/dt) _{cr}	critical rate of rise of current	T _{vJ} = 140 °C; f = 50 Hz re	epetitive, $I_{T} = 150 \text{ A}$			150	A/μ
		t_{P} = 200 µs; di _G /dt = 0.45 A/µs; -					
		$I_{G} = 0.45 \text{ A}; \text{ V} = \frac{2}{3} \text{ V}_{DRM}$ no	on-repet., $I_{\tau} = 50 \text{ A}$			500	A/μ
(dv/dt) _{cr}	critical rate of rise of voltage	$V = \frac{2}{3} V_{\text{DBM}}$	T _{vJ} = 140°C			1000	V/µ
		R _{GK} = ∞; method 1 (linear volta	ge rise)				
V _{gt}	gate trigger voltage	$V_{\rm D} = 6 \text{ V}$	$T_{vJ} = 25^{\circ}C$			1.5	١
- 01			$T_{yJ} = -40 ^{\circ}\text{C}$			1.6	١
I _{GT}	gate trigger current	$V_{D} = 6 V$	$T_{VJ} = 25^{\circ}C$			78	m/
GI	gale ligger ear ent		$T_{vj} = -40^{\circ}C$			200	
V _{gd}	gate non-trigger voltage	$V_{D} = \frac{2}{3} V_{DBM}$	$T_{VJ} = 40^{\circ} \text{C}$ $T_{VJ} = 140^{\circ} \text{C}$			0.2	۱
	gate non-trigger current	$\mathbf{v}_{\mathrm{D}} = 73 \mathbf{v}_{\mathrm{DRM}}$	1 _{VJ} = 140 O			5	i .
		10	т огос				m/
I.	latching current	$t_p = 10 \ \mu s$	$T_{vJ} = 25 \degree C$			200	m/
_		$I_{\rm G} = 0.45 \text{A}; \text{di}_{\rm G}/\text{dt} = 0.45 \text{A}/\mu\text{s}$					
I _H	holding current	$V_{\rm D} = 6 \ V \ R_{\rm GK} = \infty$	$T_{VJ} = 25 \degree C$			100	1
t _{gd}	gate controlled delay time	$V_{D} = \frac{1}{2} V_{DRM}$	$T_{vJ} = 25 ^{\circ}C$			2	μ
		$I_{\rm G} = 0.45 \text{A}; di_{\rm G}/dt = 0.45 \text{A}/\mu \text{s}$					
t _q	turn-off time	$V_{R} = 100 \text{ V}; I_{T} = 50\text{ A}; \text{ V} = 2$	⅓ V _{DRM} T _{VJ} =125 °C		150		μ
		$di/dt = 10 \text{ A}/\mu \text{s} dv/dt = 20 \text{ V}.$	/μs t _p = 200 μs				:

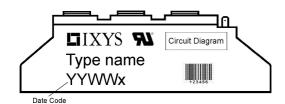
 $\ensuremath{\mathsf{IXYS}}$ reserves the right to change limits, conditions and dimensions.

20191209d



MCMA50P1200TA

Package TO-240AA				Ratings				
Symbol	Definition	Conditions			min.	typ.	max.	Unit
	RMS current	per terminal					100	Α
T _{vj}	virtual junction temperature				-40		140	°C
T _{op}	operation temperature				-40		125	°C
T _{stg}	storage temperature				-40		125	°C
Weight						81		g
M _D	mounting torque				2.5		4	Nm
M _T	terminal torque		2.5		4	Nm		
d _{Spp/App}	creepage distance on surface striking distance through		terminal to terminal	13.0	9.7			mm
d _{Spb/Apb}			terminal to backside	16.0	16.0			mm
V	isolation voltage	t = 1 second			4800			۷
	t = 1 minute		50/60 Hz, RMS; lıso∟ ≤ 1 mA		4000			V



Part description

M = Module C = Thyristor (SCR) M = Thyristor A = (up to 1800V) 50 = Current Rating [A] P = Phase leg 1200 = Reverse Voltage [V] TA = TO-240A-1B

TA = TO-240AA-1B

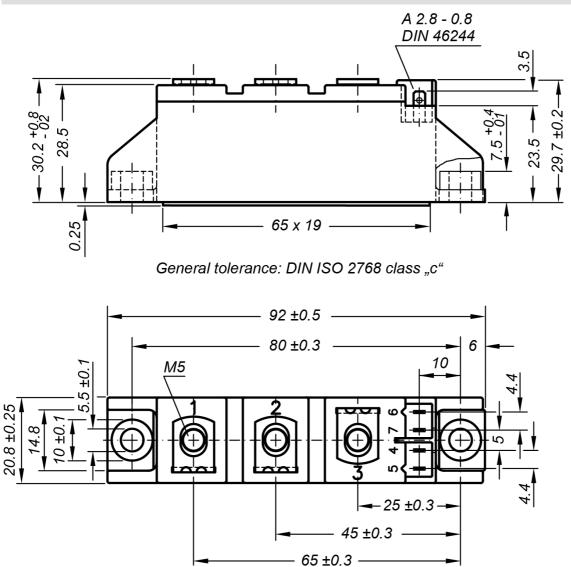
[Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
	Standard	MCMA50P1200TA	MCMA50P1200TA	Box	36	513943

Equiva	alent Circuits for	Simulation	* on die level	$T_{VJ} = 140^{\circ}C$
)[Thyristor		
V _{0 max}	threshold voltage	0.89		V
$\mathbf{R}_{0 \max}$	slope resistance *	4.1		mΩ

20191209d

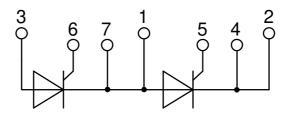


Outlines TO-240AA



Optional accessories for modules

Keyed gate/cathode twin plugs with wire length = 350 mm, gate = white, cathode = red Type ZY 200L (L = Left for pin pair 4/5) Type ZY 200R (R = Right for pin pair 6/7) UL 758, style 3751



20191209d